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Application No. Applicant(s) 09/414,520

Takahashi et ai

	Median of Dafa	range Cited	U9/414,	520	i akanasni et ai			
	Notice of Refer	ences Cited	Examine	Examiner Rudy Zervigon			Group Art Unit 1763 P	
_			U.S. PATENT DOCUM	ENTS				
	DOCUMENT NO.	DATE	·	NAME			CLASS	SUBCLASS
А	5,961,850	10/1999	Satou et al 216					67
В	5,429,070	7/1995	C	Campbell et al 118				
С	6,015,465	1/2000	Kholodenko et al 11					719
D	5,254,171	10/1993	Hayakawa et al 11					723MR
E	5,589,041	10/1999	Lantsman 20				204	192.33
F		-						
G								
н								
1								
J								
к						i.		
L								
м								
!		F	OREIGN PATENT DOC	JMENTS				
	DOCUMENT NO.	DATE	COUNTRY		NAME		CLASS	SUBCLAS
N								
0				<u>-</u>				
Р			<u> </u>					
a								
R								
5								
Т								
			NON-PATENT DOCUM	IENTS	-			
DOCUMENT (Including Author, Title, Source, and Pertinent Pages)								
u	Hancock et al, "Time-Resolved Fourier transform infrared emission as a plama diagnostic" J. Vac. Sci. Technol. A 13(6), Nov/Dec 1995, pp2945-2949							
v	Uhm et al, "A theoretical model of bulk plasma generated by the electron-cyclotron-resonance mechanism", Physics of Fluids B: Plasma Physics 5(6), June 1993, pp.1902-1910 <abstract></abstract>							
w	Etrillard et al, "Anisotropic etching of InP with low sidewall and surface induced damage in inductively coupled plasma etching using CF4", J.Vac.Sci.Technol.A 15(3), May/Jun 1997 pp 626-632							6/1997
x	Nishino et al, "Smoothing	of the Si surface using	g CF4/O2 down-flow et	ching", J.A	Appl.Phys. 74	(2)pp.1349-135	3	7/1993

U. S. Patent and Trademark Office PTO-892 (Rev. 9-95)